

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Peng Cheng, et al

Application No.: 09/343,293

Filed: June 30, 1999

For: Transistor Structure Having Silicide
Source/Drain Extensions And Method
For Making Same

Examiner: E. Ortiz

Art Unit: 2815

Docket No.: 42390.P7068

I hereby certify that this correspondence is being deposited with the
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Washington, D.C. 20231 on:

April 25, 2000

Mary E. Warriner

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Signature

Date

AMENDMENT AND RESPONSE

Honorable Commissioner
of Patents and Trademarks
Washington, DC 20231

Sir:

In response to the Office Action mailed March 30, 2000, please amend
the above-identified application as follows.

IN THE CLAIMS

Please cancel Claims 1-17.

Please amend Claim 18 as follows:

- 1 18. (Amended) A microelectronic structure, comprising:
- 2 a gate electrode having sidewalls;
- 3 a silicidation barrier adjacent to the sidewalls;
- 4 a first silicide layer superjacent the gate electrode; and
- 5 a pair of source/drain terminals self-aligned to the gate electrode;

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